

Fabrizio Roccaforte

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

332
papers

5,803
citations

42
h-index

60
g-index

350
ext. papers

6,603
ext. citations

2.4
avg, IF

5.92
L-index

#	Paper	IF	Citations
332	Structural and Insulating Behaviour of High-Permittivity Binary Oxide Thin Films for Silicon Carbide and Gallium Nitride Electronic Devices.. <i>Materials</i> , 2022 , 15,	3.5	2
331	Ion Implantation Doping in Silicon Carbide and Gallium Nitride Electronic Devices. <i>Micro</i> , 2022 , 2, 23-53		4
330	Early Growth Stages of Aluminum Oxide (Al ₂ O ₃) Insulating Layers by Thermal- and Plasma-Enhanced Atomic Layer Deposition on AlGa _N /Ga _N Heterostructures. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 406-415	4	2
329	Temperature and time dependent electron trapping in Al ₂ O ₃ thin films onto AlGa _N /Ga _N heterostructures. <i>Applied Surface Science</i> , 2022 , 579, 152136	6.7	2
328	Nanoscale structural and electrical properties of graphene grown on AlGa _N by catalyst-free chemical vapor deposition. <i>Nanotechnology</i> , 2021 , 32, 015705	3.4	0
327	Substrate-Driven Atomic Layer Deposition of High-Dielectrics on 2D Materials. <i>Applied Sciences (Switzerland)</i> , 2021 , 11, 11052	2.6	1
326	Direct Atomic Layer Deposition of Ultrathin Aluminum Oxide on Monolayer MoS ₂ Exfoliated on Gold: The Role of the Substrate. <i>Advanced Materials Interfaces</i> , 2021 , 8, 2101117	4.6	2
325	Status and Prospects of Cubic Silicon Carbide Power Electronics Device Technology. <i>Materials</i> , 2021 , 14,	3.5	2
324	Status of 3 C - SiC Growth and Device Technology 2021 , 93-136		
323	Electrical properties of inhomogeneous tungsten carbide Schottky barrier on 4H-SiC. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 055101	3	7
322	Forward and reverse current transport mechanisms in tungsten carbide Schottky contacts on AlGa _N /Ga _N heterostructures. <i>Journal of Applied Physics</i> , 2021 , 129, 234501	2.5	3
321	High-Resolution Two-Dimensional Imaging of the 4H-SiC MOSFET Channel by Scanning Capacitance Microscopy. <i>Nanomaterials</i> , 2021 , 11,	5.4	3
320	Strain, Doping, and Electronic Transport of Large Area Monolayer MoS ₂ Exfoliated on Gold and Transferred to an Insulating Substrate. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 31248-31259	9.5	7
319	Selective Doping in Silicon Carbide Power Devices. <i>Materials</i> , 2021 , 14,	3.5	7
318	Substrate impact on the thickness dependence of vibrational and optical properties of large area MoS ₂ produced by gold-assisted exfoliation. <i>Applied Physics Letters</i> , 2021 , 119, 093103	3.4	5
317	Interfacial electrical and chemical properties of deposited SiO ₂ layers in lateral implanted 4H-SiC MOSFETs subjected to different nitridations. <i>Applied Surface Science</i> , 2021 , 557, 149752	6.7	6
316	Ni Schottky barrier on heavily doped phosphorous implanted 4H-SiC. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 445107	3	8

315	Barrier height tuning in Ti/4H-SiC Schottky diodes. <i>Solid-State Electronics</i> , 2021 , 186, 108042	1.7	6
314	Materials and Processes for Schottky Contacts on Silicon Carbide.. <i>Materials</i> , 2021 , 15,	3.5	1
313	Current Transport Mechanisms in Au-Free Metallizations for CMOS Compatible GaN HEMT Technology. <i>Materials Science Forum</i> , 2020 , 1004, 725-730	0.4	
312	Nanolaminated Al ₂ O ₃ /HfO ₂ dielectrics for silicon carbide based devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 032410	2.9	2
311	Impact of Stacking Faults and Domain Boundaries on the Electronic Transport in Cubic Silicon Carbide Probed by Conductive Atomic Force Microscopy. <i>Advanced Electronic Materials</i> , 2020 , 6, 1901171	6.4	16
310	Genesis and evolution of extended defects: The role of evolving interface instabilities in cubic SiC. <i>Applied Physics Reviews</i> , 2020 , 7, 021402	17.3	22
309	Atomic Layer Deposition of High-k Insulators on Epitaxial Graphene: A Review. <i>Applied Sciences (Switzerland)</i> , 2020 , 10, 2440	2.6	7
308	Conductive Atomic Force Microscopy of Semiconducting Transition Metal Dichalcogenides and Heterostructures. <i>Nanomaterials</i> , 2020 , 10,	5.4	17
307	Correlating electron trapping and structural defects in Al ₂ O ₃ thin films deposited by plasma enhanced atomic layer deposition. <i>AIP Advances</i> , 2020 , 10, 125017	1.5	7
306	On the origin of the premature breakdown of thermal oxide on 3C-SiC probed by electrical scanning probe microscopy. <i>Applied Surface Science</i> , 2020 , 526, 146656	6.7	4
305	Extensive Fermi-Level Engineering for Graphene through the Interaction with Aluminum Nitrides and Oxides. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 1900399	2.5	4
304	Ni/4H-SiC interaction and silicide formation under excimer laser annealing for ohmic contact. <i>Materialia</i> , 2020 , 9, 100528	3.2	10
303	Understanding the role of threading dislocations on 4H-SiC MOSFET breakdown under high temperature reverse bias stress. <i>Nanotechnology</i> , 2020 , 31, 125203	3.4	9
302	Aluminum oxide nucleation in the early stages of atomic layer deposition on epitaxial graphene. <i>Carbon</i> , 2020 , 169, 172-181	10.4	11
301	Active dopant profiling and Ohmic contacts behavior in degenerate n-type implanted silicon carbide. <i>Applied Physics Letters</i> , 2020 , 117, 013502	3.4	6
300	Thermal annealing effect on electrical and structural properties of Tungsten Carbide Schottky contacts on AlGaIn/GaN heterostructures. <i>Semiconductor Science and Technology</i> , 2020 , 35, 105004	1.8	2
299	Nanoscale Insights on the Origin of the Power MOSFETs Breakdown after Extremely Long High Temperature Reverse Bias Stress. <i>Materials Science Forum</i> , 2020 , 1004, 433-438	0.4	1
298	Introduction to Gallium Nitride Properties and Applications 2020 , 1-39		3

297	Technologies for Normally-off GaN HEMTs 2020 , 137-175		
296	Reliability Issues in GaN Electronic Devices 2020 , 199-252		2
295	Integration of 2D Materials with Nitrides for Novel Electronic and Optoelectronic Applications 2020 , 397-438		2
294	Identification of two trapping mechanisms responsible of the threshold voltage variation in SiO ₂ /4H-SiC MOSFETs. <i>Applied Physics Letters</i> , 2020 , 117, 103502	3-4	5
293	Direct Probing of Grain Boundary Resistance in Chemical Vapor Deposition-Grown Monolayer MoS ₂ by Conductive Atomic Force Microscopy. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 1900393	2-5	15
292	Comparison between thermal and plasma enhanced atomic layer deposition processes for the growth of HfO ₂ dielectric layers. <i>Journal of Crystal Growth</i> , 2020 , 539, 125624	1-6	15
291	Growth and characterization of thin Al-rich AlGa _{0.1} N on bulk GaN as an emitter-base barrier for hot electron transistor. <i>Materials Science in Semiconductor Processing</i> , 2019 , 93, 153-157	4-3	6
290	Ohmic contacts on n-type and p-type cubic silicon carbide (3C-SiC) grown on silicon. <i>Materials Science in Semiconductor Processing</i> , 2019 , 93, 295-298	4-3	7
289	Effect of high temperature annealing (T > 1650 °C) on the morphological and electrical properties of p-type implanted 4H-SiC layers. <i>Materials Science in Semiconductor Processing</i> , 2019 , 93, 274-279	4-3	20
288	Characterization of SiO ₂ /4H-SiC Interfaces in 4H-SiC MOSFETs: A Review. <i>Energies</i> , 2019 , 12, 2310	3-1	44
287	An Overview of Normally-Off GaN-Based High Electron Mobility Transistors. <i>Materials</i> , 2019 , 12,	3-5	92
286	Seed-Layer-Free Atomic Layer Deposition of Highly Uniform Al ₂ O ₃ Thin Films onto Monolayer Epitaxial Graphene on Silicon Carbide. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1900097	4-6	15
285	Properties of Al ₂ O ₃ thin films deposited on 4H-SiC by reactive ion sputtering. <i>Materials Science in Semiconductor Processing</i> , 2019 , 93, 290-294	4-3	7
284	Morphological and electrical properties of Nickel based Ohmic contacts formed by laser annealing process on n-type 4H-SiC. <i>Materials Science in Semiconductor Processing</i> , 2019 , 97, 62-66	4-3	16
283	Structural and electrical properties of AlN thin films on GaN substrates grown by plasma enhanced-Atomic Layer Deposition. <i>Materials Science in Semiconductor Processing</i> , 2019 , 97, 35-39	4-3	7
282	Barrier inhomogeneity in vertical Schottky diodes on free standing gallium nitride. <i>Materials Science in Semiconductor Processing</i> , 2019 , 94, 164-170	4-3	17
281	Conductive AFM of 2D Materials and Heterostructures for Nanoelectronics. <i>Nanoscience and Technology</i> , 2019 , 303-350	0-6	6
280	Metal/Semiconductor Barrier Properties of Non-Recessed Ti/Al/Ti and Ta/Al/Ta Ohmic Contacts on AlGa _{0.1} N/GaN Heterostructures. <i>Energies</i> , 2019 , 12, 2655	3-1	7

279	High-Performance Graphene/AlGaIn/GaN Schottky Junctions for Hot Electron Transistors. <i>ACS Applied Electronic Materials</i> , 2019 , 1, 2342-2354	4	23
278	Ohmic Contacts on p-Type Al-Implanted 4H-SiC Layers after Different Post-Implantation Annealings. <i>Materials</i> , 2019 , 12,	3.5	8
277	Recent Advances in Seeded and Seed-Layer-Free Atomic Layer Deposition of High-K Dielectrics on Graphene for Electronics. <i>Journal of Carbon Research</i> , 2019 , 5, 53	3.3	12
276	Effects of Thermal Annealing Processes in Phosphorous Implanted 4H-SiC Layers. <i>Materials Science Forum</i> , 2019 , 963, 407-411	0.4	6
275	Fabrication and Characterization of Ohmic Contacts to 3C-SiC Layers Grown on Silicon. <i>Materials Science Forum</i> , 2019 , 963, 485-489	0.4	2
274	SiO ₂ /SiC MOSFETs Interface Traps Probed by Nanoscale Analyses and Transient Current and Capacitance Measurements. <i>Materials Science Forum</i> , 2019 , 963, 230-235	0.4	
273	Electrical Properties of Thermal Oxide on 3C-SiC Layers Grown on Silicon. <i>Materials Science Forum</i> , 2019 , 963, 479-482	0.4	2
272	Electrical Characterisation of Thick 3C-SiC Layers Grown on Off-Axis 4H-SiC Substrates. <i>Materials Science Forum</i> , 2019 , 963, 353-356	0.4	
271	Temperature-dependent Fowler-Nordheim electron barrier height in SiO ₂ /4H-SiC MOS capacitors. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 38-42	4.3	17
270	Determining oxide trapped charges in Al ₂ O ₃ insulating films on recessed AlGaIn/GaN heterostructures by gate capacitance transients measurements. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 050307	1.4	9
269	Barrier Inhomogeneity of Ni Schottky Contacts to Bulk GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700613	1.6	11
268	Review of technology for normally-off HEMTs with p-GaN gate. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 96-106	4.3	95
267	Nanoscale electrical mapping of two-dimensional materials by conductive atomic force microscopy for transistors applications 2018 ,		4
266	Electron trapping at SiO ₂ /4H-SiC interface probed by transient capacitance measurements and atomic resolution chemical analysis. <i>Nanotechnology</i> , 2018 , 29, 395702	3.4	10
265	Vertical Transistors Based on 2D Materials: Status and Prospects. <i>Crystals</i> , 2018 , 8, 70	2.3	56
264	Temperature-Dependence Study of the Gate Current SiO ₂ /4H-SiC MOS Capacitors. <i>Materials Science Forum</i> , 2018 , 924, 473-476	0.4	
263	3C-SiC Hetero-Epitaxially Grown on Silicon Compliance Substrates and New 3C-SiC Substrates for Sustainable Wide-Band-Gap Power Devices (CHALLENGE). <i>Materials Science Forum</i> , 2018 , 924, 913-918	0.4	10
262	Hot Electron Transistors with Graphene Base for THz Electronics 2018 , 95-115		2

261	Modification of the sheet resistance under Ti/Al/Ni/Au Ohmic contacts on AlGaIn/GaN heterostructures. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 111-117	4.3	11
260	Emerging trends in wide band gap semiconductors (SiC and GaN) technology for power devices. <i>Microelectronic Engineering</i> , 2018 , 187-188, 66-77	2.5	163
259	Fabrication and Characterization of Graphene Heterostructures with Nitride Semiconductors for High Frequency Vertical Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700653	1.6	14
258	Oxide Traps Probed by Transient Capacitance Measurements on Lateral SiO ₂ /4H-SiC MOSFETs. <i>Materials Science Forum</i> , 2018 , 924, 285-288	0.4	2
257	Processing Issues in SiC and GaN Power Devices Technology: The Cases of 4H-SiC Planar MOSFET and Recessed Hybrid GaN MISHEMT 2018 ,		2
256	Metal/Semiconductor Contacts to Silicon Carbide: Physics and Technology. <i>Materials Science Forum</i> , 2018 , 924, 339-344	0.4	7
255	Study of Ti/Al/Ni Ohmic Contacts to p-Type Implanted 4H-SiC. <i>Materials Science Forum</i> , 2018 , 924, 377-380	0.4	1
254	Interface Electrical Properties of AlO Thin Films on Graphene Obtained by Atomic Layer Deposition with an in Situ Seedlike Layer. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 7761-7771	9.5	33
253	Temperature dependent forward current-voltage characteristics of Ni/Au Schottky contacts on AlGaIn/GaN heterostructures described by a two diodes model. <i>Journal of Applied Physics</i> , 2017 , 121, 045701	2.5	15
252	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. <i>Carbon</i> , 2017 , 116, 722-732	10.4	21
251	Temperature dependence of the I _V characteristics of Ni/Au Schottky contacts to AlGaIn/GaN heterostructures grown on Si substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600764	1.6	3
250	Channel Mobility in GaN Hybrid MOS-HEMT Using SiO ₂ as Gate Insulator. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2893-2899	2.9	27
249	Properties of SiO ₂ /4H-SiC Interfaces with an Oxide Deposited by a High-Temperature Process. <i>Materials Science Forum</i> , 2017 , 897, 331-334	0.4	2
248	Electrical and structural properties of surfaces and interfaces in Ti/Al/Ni Ohmic contacts to p-type implanted 4H-SiC. <i>Applied Surface Science</i> , 2017 , 420, 331-335	6.7	20
247	Anomalous Fowler-Nordheim Tunneling through SiO ₂ /4H-SiC Barrier Investigated by Temperature and Time Dependent Gate Current Measurements. <i>Materials Science Forum</i> , 2017 , 897, 123-126	0.4	
246	Ambipolar MoS Transistors by Nanoscale Tailoring of Schottky Barrier Using Oxygen Plasma Functionalization. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 23164-23174	9.5	62
245	Effect of SiO ₂ interlayer on the properties of Al ₂ O ₃ thin films grown by plasma enhanced atomic layer deposition on 4H-SiC substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600365	1.6	7
244	Plasma enhanced atomic layer deposition of Al ₂ O ₃ gate dielectric thin films on AlGaIn/GaN substrates: The role of surface predeposition treatments. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017 , 35, 01B140	2.9	5

243	Effects of interface states and near interface traps on the threshold voltage stability of GaN and SiC transistors employing SiO ₂ as gate dielectric. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 01A101	1.3	16
242	Advances in the fabrication of graphene transistors on flexible substrates. <i>Beilstein Journal of Nanotechnology</i> , 2017 , 8, 467-474	3	16
241	Conductive Atomic Force Microscopy of Two-Dimensional Electron Systems: From AlGaIn/GaN Heterostructures to Graphene and MoS ₂ 2017 , 163-185		7
240	Conduction Mechanisms at Interface of AlN/SiN Dielectric Stacks with AlGaIn/GaN Heterostructures for Normally-off High Electron Mobility Transistors: Correlating Device Behavior with Nanoscale Interfaces Properties. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 35383-35390	9.5	21
239	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P741-P745	2	
238	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Transactions</i> , 2017 , 80, 107-115		1
237	Ti/Al-based contacts to p-type SiC and GaN for power device applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600357	1.6	12
236	Graphene integration with nitride semiconductors for high power and high frequency electronics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600460	1.6	33
235	Impact of contact resistance on the electrical properties of MoS transistors at practical operating temperatures. <i>Beilstein Journal of Nanotechnology</i> , 2017 , 8, 254-263	3	29
234	In-situ monitoring by Raman spectroscopy of the thermal doping of graphene and MoS in O ₂ -controlled atmosphere. <i>Beilstein Journal of Nanotechnology</i> , 2017 , 8, 418-424	3	10
233	Advances in the Fabrication of Large-Area Back-Gated Graphene Field-Effect Transistors on Plastics: Platform for Flexible Electronics and Sensing. <i>Carbon Nanostructures</i> , 2017 , 125-136	0.6	
232	Electrical characterization of trapping phenomena at SiO ₂ /SiC and SiO ₂ /GaN in MOS-based devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600366	1.6	4
231	Current injection from metal to MoS ₂ probed at nanoscale by conductive atomic force microscopy. <i>Materials Science in Semiconductor Processing</i> , 2016 , 42, 174-178	4.3	9
230	Effect of temperature bias annealing on the hysteresis and subthreshold behavior of multilayer MoS ₂ transistors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016 , 10, 797-801	2.5	23
229	Processing and Characterization of MOS Capacitors Fabricated on 2 ^θ -Off Axis 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2016 , 858, 663-666	0.4	
228	Conduction Mechanisms at SiO ₂ /4H-SiC Interfaces in MOS-Based Devices Subjected to Post Deposition Annealing in N ₂ O. <i>Materials Science Forum</i> , 2016 , 858, 705-708	0.4	
227	Nanoscale probing of the lateral homogeneity of donors concentration in nitridated SiO ₂ /4H-SiC interfaces. <i>Nanotechnology</i> , 2016 , 27, 315701	3.4	9
226	Interfacial Disorder of Graphene Grown at High Temperatures on 4H-SiC(000-1). <i>Materials Science Forum</i> , 2016 , 858, 1129-1132	0.4	

225	X-Ray Irradiation on 4H-SiC MOS Capacitors Processed under Different Annealing Conditions. <i>Materials Science Forum</i> , 2016 , 858, 659-662	0.4	1
224	Impact of Phosphorus Implantation on the Electrical Properties of SiO ₂ /4H-SiC Interfaces Annealed in N ₂ O. <i>Materials Science Forum</i> , 2016 , 858, 701-704	0.4	1
223	Effect of air on oxygen p-doped graphene on SiO ₂ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 2341-2344	1.6	21
222	Metal/P-GaN Contacts on AlGaN/GaN Heterostructures for Normally-Off HEMTs. <i>Materials Science Forum</i> , 2016 , 858, 1170-1173	0.4	6
221	Atomic Layer Deposition of Al ₂ O ₃ Thin Films for Metal Insulator Semiconductor Applications on 4H-SiC. <i>Materials Science Forum</i> , 2016 , 858, 685-688	0.4	2
220	Ni ₂ Si/4H-SiC Schottky Photodiodes for Ultraviolet Light Detection. <i>Materials Science Forum</i> , 2016 , 858, 1015-1018	0.4	
219	Electrical properties of SiO ₂ /SiC interfaces on 2 $\bar{1}$ -off axis 4H-SiC epilayers. <i>Applied Surface Science</i> , 2016 , 364, 892-895	6.7	5
218	Effects of Annealing Treatments on the Properties of Al/Ti/p-GaN Interfaces for Normally OFF p-GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2735-2741	2.9	39
217	Trapping States in SiO ₂ /GaN MOS Capacitors Fabricated on Recessed AlGaN/GaN Heterostructures. <i>Materials Science Forum</i> , 2016 , 858, 1178-1181	0.4	
216	Laminated Al ₂ O ₃ /HfO ₂ layers grown by atomic layer deposition for microelectronics applications. <i>Thin Solid Films</i> , 2016 , 601, 68-72	2.2	9
215	Surface treatments on AlGaN/GaN heterostructures for gate dielectric Al ₂ O ₃ thin films grown by Atomic Layer Deposition. <i>Thin Solid Films</i> , 2016 , 617, 138-142	2.2	8
214	Challenges in graphene integration for high-frequency electronics 2016 ,		2
213	Large Area Visible Blind 4H-SiC p+/N UV Photodiode Obtained by Aluminium Implantation. <i>Materials Science Forum</i> , 2016 , 858, 1019-1022	0.4	
212	Near interface traps in SiO ₂ /4H-SiC metal-oxide-semiconductor field effect transistors monitored by temperature dependent gate current transient measurements. <i>Applied Physics Letters</i> , 2016 , 109, 012102	3.4	26
211	Negative charge trapping effects in Al ₂ O ₃ films grown by atomic layer deposition onto thermally oxidized 4H-SiC. <i>AIP Advances</i> , 2016 , 6, 075021	1.5	28
210	Effect of germanium doping on electrical properties of n-type 4H-SiC homoepitaxial layers grown by chemical vapor deposition. <i>Journal of Applied Physics</i> , 2016 , 120, 205701	2.5	5
209	Hot Electron Transistors Based on Graphene/AlGaN/GaN Vertical Heterostructures. <i>Materials Science Forum</i> , 2016 , 858, 1137-1140	0.4	5
208	Ohmic contacts to Gallium Nitride materials. <i>Applied Surface Science</i> , 2016 , 383, 324-345	6.7	153

207	Atomistic Simulations and Interfacial Morphology of Graphene Grown on SiC(0001) and SiC(000-1) Substrates. <i>Materials Science Forum</i> , 2016 , 858, 1121-1124	0.4	
206	Substrate and atmosphere influence on oxygen p-doped graphene. <i>Carbon</i> , 2016 , 107, 696-704	10.4	13
205	Electrical Properties of Graphene Contacts to AlGa _N /Ga _N Heterostructures. <i>Materials Science Forum</i> , 2015 , 821-823, 986-989	0.4	
204	Evolution of the Electrical and Structural Properties of Ti/Al/W Contacts to p-Type Implanted 4H-SiC upon Thermal Annealing. <i>Materials Science Forum</i> , 2015 , 821-823, 428-431	0.4	
203	An insight into the epitaxial nanostructures of NiO and CeO ₂ thin film dielectrics for AlGa _N /Ga _N heterostructures. <i>Materials Chemistry and Physics</i> , 2015 , 162, 461-468	4.4	10
202	Slow and fast traps in metal-oxide-semiconductor capacitors fabricated on recessed AlGa _N /Ga _N heterostructures. <i>Applied Physics Letters</i> , 2015 , 106, 142903	3.4	30
201	. <i>IEEE Photonics Journal</i> , 2015 , 7, 1-6	1.8	15
200	Microstructure and Temperature Dependent Electrical Characteristics of Ohmic Contacts to AlGa _N /Ga _N Heterostructures. <i>Materials Science Forum</i> , 2015 , 821-823, 999-1002	0.4	
199	Preliminary Study on the Effect of Micrometric Ge-Droplets on the Characteristics of Ni/4H-SiC Schottky Contacts. <i>Materials Science Forum</i> , 2015 , 821-823, 424-427	0.4	
198	Industrial Approach for Next Generation of Power Devices Based on 4H-SiC. <i>Materials Science Forum</i> , 2015 , 821-823, 660-666	0.4	4
197	Electrical Properties of Hydrogen Intercalated Epitaxial Graphene/SiC Interface Investigated by Nanoscale Current Mapping. <i>Materials Science Forum</i> , 2015 , 821-823, 929-932	0.4	5
196	Graphene p-Type Doping and Stability by Thermal Treatments in Molecular Oxygen Controlled Atmosphere. <i>Journal of Physical Chemistry C</i> , 2015 , 119, 22718-22723	3.8	36
195	Nanoscale inhomogeneity of the Schottky barrier and resistivity in MoS ₂ multilayers. <i>Physical Review B</i> , 2015 , 92,	3.3	58
194	Ti/Al/W Ohmic contacts to p-type implanted 4H-SiC. <i>Journal of Applied Physics</i> , 2015 , 118, 035705	2.5	24
193	Effects of surface nature of different semiconductor substrates on the plasma enhanced atomic layer deposition growth of Al ₂ O ₃ gate dielectric thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 980-984		5
192	Electrical and structural properties of Ti/Al-based contacts on AlGa _N /Ga _N heterostructures with different quality. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 1091-1098	1.6	4
191	Metal Organic Chemical Vapor Deposition of nickel oxide thin films for wide band gap device technology. <i>Thin Solid Films</i> , 2014 , 563, 50-55	2.2	25
190	Current transport in graphene/AlGa _N /Ga _N vertical heterostructures probed at nanoscale. <i>Nanoscale</i> , 2014 , 6, 8671-80	7.7	57

189	Nanoscale electrical and structural modification induced by rapid thermal oxidation of AlGa _N /Ga _N heterostructures. <i>Nanotechnology</i> , 2014 , 25, 025201	3.4	19
188	Ti/Al ohmic contacts on AlGa _N /Ga _N heterostructures with different defect density. <i>Applied Surface Science</i> , 2014 , 314, 546-551	6.7	24
187	Microscopic mechanisms of graphene electrolytic delamination from metal substrates. <i>Applied Physics Letters</i> , 2014 , 104, 233105	3.4	45
186	Thermal stability of the current transport mechanisms in Ni-based Ohmic contacts on n- and p-implanted 4H-SiC. <i>Semiconductor Science and Technology</i> , 2014 , 29, 075018	1.8	42
185	Challenges for energy efficient wide band gap semiconductor power devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 2063-2071	1.6	78
184	High resolution study of structural and electronic properties of epitaxial graphene grown on off-axis 4H-SiC (0001). <i>Journal of Crystal Growth</i> , 2014 , 393, 150-155	1.6	9
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27	Effects of CD2 locus control region sequences on gene expression by retroviral and lentiviral vectors. <i>Blood</i> , 2001 , 98, 3607-17	2.2	28
26	Dopant profile measurements in ion implanted 6H-SiC by scanning capacitance microscopy. <i>Applied Surface Science</i> , 2001 , 184, 183-189	6.7	9
25	Crystallisation mechanism of amorphous silicon carbide. <i>Applied Surface Science</i> , 2001 , 184, 123-127	6.7	33
24	Improvement of high temperature stability of nickel contacts on n-type 6H-SiC. <i>Applied Surface Science</i> , 2001 , 184, 295-298	6.7	58
23	Ion beam doping and epitaxial regrowth of α -quartz. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2001 , 178, 237-241	1.2	3
22	Angular distortion of Si clusters in a-SiC. <i>Europhysics Letters</i> , 2001 , 55, 674-678	1.6	18
21	Ion-Irradiation Effect on the Ni/SiC Interface Reaction. <i>Materials Science Forum</i> , 2001 , 353-356, 255-258	0.4	4
20	Epitaxial crystallization of keV-ion-bombarded α -quartz. <i>Journal of Applied Physics</i> , 2001 , 89, 3611-3618	2.5	19
19	Structural and Electrical Characterisation of Nickel Silicides Contacts on Silicon Carbide. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 680, 1		
18	Epitaxial recrystallization of alkali-ion implanted α -quartz. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000 , 166-167, 148-153	1.2	7
17	Diffusion of hydrogen implanted in α -quartz during air annealing. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000 , 161-163, 641-645	1.2	5
16	Ion beam erosion of graphite surfaces studied by STM: Ripples, self-affine roughening and near-surface damage accumulation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000 , 161-163, 958-962	1.2	19
15	Ripple topography of ion-beam-eroded graphite: A key to ion-beam-induced damage tracks. <i>Europhysics Letters</i> , 2000 , 50, 209-215	1.6	38
14	Oxygen-activated epitaxial recrystallization of Li-implanted SiO ₂ . <i>Physical Review B</i> , 2000 , 61, 3327-3332	3.3	24
13	Oxygen migration during epitaxial regrowth in Cs ⁺ -irradiated α -quartz investigated by means of nuclear reaction analysis. <i>Applied Physics Letters</i> , 2000 , 76, 3709-3711	3.4	18
12	Nonlinear analysis of beams under electrostatic loads	2000, 4019, 90	2
11	Epitaxial crystallization of amorphous SiO ₂ films deposited on single-crystalline α -quartz. <i>Applied Physics Letters</i> , 1999 , 75, 2903-2905	3.4	20
10	Addendum: Solid phase epitaxial regrowth in ion-beam-amorphized α -quartz [Appl. Phys. Lett. 73, 1349 (1998)]. <i>Applied Physics Letters</i> , 1999 , 74, 1922-1922	3.4	8

9	Network modification and epitaxial recrystallisation of ion-implanted β -quartz. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1999 , 148, 692-697	1.2	14
8	Solid phase epitaxial regrowth of ion beam-amorphized β -quartz. <i>Applied Physics Letters</i> , 1998 , 73, 1349-1351	1.3	39
7	Relaxation and crystallization of amorphous silicon carbide probed by optical measurements. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1997 , 76, 323-333		57
6	Optical transient in ion irradiated silicon carbide. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1997 , 127-128, 360-363	1.2	2
5	Electrical evolution of W and WC Schottky contacts on 4H-SiC at different annealing temperatures. <i>Semiconductor Science and Technology</i> ,	1.8	2
4	Charge Trapping Mechanisms in Nitridated SiO_2 / 4H-SiC MOSFET Interfaces: Threshold Voltage Instability and Interface Chemistry. <i>Materials Science Forum</i> ,1062, 160-164	0.4	
3	High Temperature Etching for Threading Dislocation Investigation on GaN Epi-Layer. <i>Materials Science Forum</i> ,1062, 18-22	0.4	
2	Electrical Scanning Probe Microscopy Investigation of Schottky and Metal-Oxide Junctions on Hetero-Epitaxial 3C-SiC/Silicon. <i>Materials Science Forum</i> ,1062, 400-405	0.4	
1	Ni/Heavily-Doped 4H-SiC Schottky Contacts. <i>Materials Science Forum</i> ,1062, 411-416	0.4	